

DRYING PROCESSING METHOD AND APPARATUS USING SAMEABSTRACT OF THE DISCLOSURE

A drying processing apparatus for supplying a dry gas to a processing chamber 35, which houses therein semiconductor wafers W, to dry the semiconductor wafers W, comprises: a heater 32 for heating N₂ gas serving as a carrier gas; a vapor generator 34 for making IPA misty by using the N₂ gas heated by the heater 32 and for heating the IPA to produce said dry gas; and a flow control element 36 for supplying a predetermined rate of N₂ gas to the processing chamber 35. Thus, it is possible to improve the efficiency of heat transfer of N₂ gas, and it is possible to increase the amount of produced IPA gas and decrease the time to produce IPA gas. In addition, it is possible to prevent the turbulence of atmosphere in the processing chamber 35 after the drying processing is completed.

(Fig. 3)